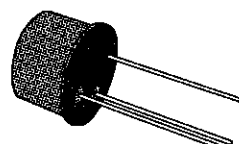


GENERAL PURPOSE TRANSISTORS

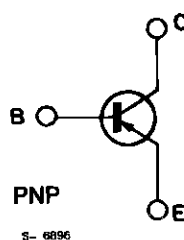
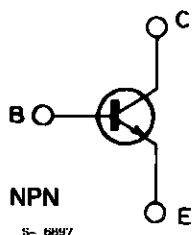
DESCRIPTION

The BC140 and BC141 are silicon planar epitaxial NPN transistors in TO-39 metal case. They are particularly designed for audio amplifiers and switching applications up to 1 A. The complementary PNP types are the BC160 and BC161.



TO-39

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		BC140	BC141	
V_{CBO}	Collector-base Voltage ($I_E = 0$)	80	100	V
V_{CEO}	Collector-emitter Voltage ($I_B = 0$)	40	60	V
V_{EBO}	Emitter-base Voltage ($I_C = 0$)	7		V
I_C	Collector Current	1		A
I_B	Base Current	0.1		A
P_{tot}	Total Power Dissipation at $T_{amb} \leq 45^\circ\text{C}$ at $T_{case} \leq 45^\circ\text{C}$	0.65 3.7		W W
T_{stg}	Storage Temperature	- 55 to 175		$^\circ\text{C}$
T_j	Junction Temperature	175		$^\circ\text{C}$

BC140-BC141

THERMAL DATA

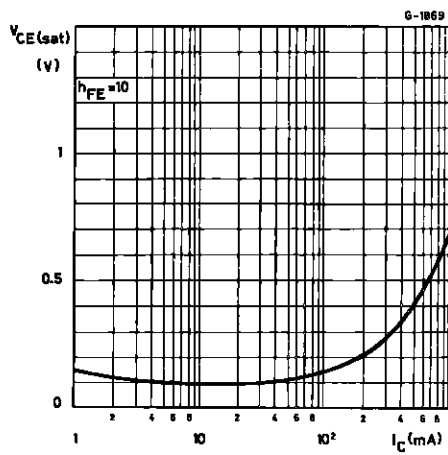
$R_{th\ j-case}$	Thermal Resistance Junction-case	Max	35	$^{\circ}C/W$
$R_{th\ j-amb}$	Thermal Resistance Junction-ambient	Max	200	$^{\circ}C/W$

ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}C$ unless otherwise specified)

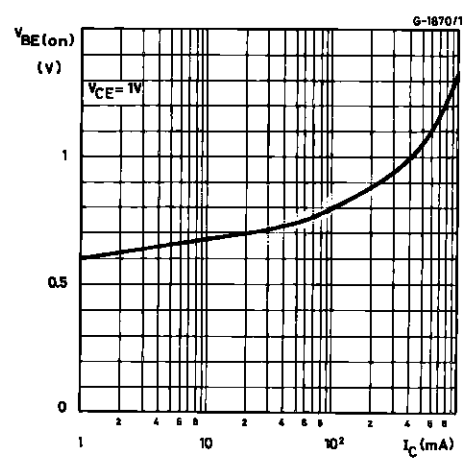
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CES}	Collector Cutoff Current ($I_E = 0$)	$V_{CES} = 60\ V$ $V_{CES} = 60\ V$ $T_{amb} = 150^{\circ}C$			100 100	nA μA
$V_{(BR)CBO}$	Collector-base Breakdown Voltage ($I_E = 0$)	$I_C = 100\ \mu A$ for BC140 for BC141	80 100			V V
$V_{(BR)CEO}^*$	Collector-emitter Breakdown Voltage ($I_B = 0$)	$I_C = 30\ mA$ for BC140 for BC141	40 60			V V
$V_{(BR)EBO}$	Emitter-base Breakdown Voltage ($I_C = 0$)	$I_E = 100\ \mu A$	7			V
$V_{CE(sat)}^*$	Collector-emitter Saturation Voltage	$I_C = 100\ mA$ $I_B = 10\ mA$ $I_C = 500\ mA$ $I_B = 50\ mA$ $I_C = 1\ A$ $I_B = 0.1\ A$		0.1 0.35 0.6	1	V V V
V_{BE}^*	Base-emitter Voltage	$I_C = 1\ A$ $V_{CE} = 1\ V$		1.25	1.8	V
h_{FE}^*	DC Current Gain	$I_C = 100\ \mu A$ $V_{CE} = 1\ V$ for BC140-141 for BC140-141 Gr. 6 for BC140-141 Gr. 10 for BC140-141 Gr. 16 $I_C = 100\ mA$ $V_{CE} = 1\ V$ for BC140-141 for BC140-141 Gr. 6 for BC140-141 Gr.10 for BC140-141 Gr.16 $I_C = 1\ A$ $V_{CE} = 1\ V$ for BC140-141 for BC140-141 Gr. 6 for BC140-141 Gr.10 for BC140-141 Gr.16		75 28 40 90 40 40 63 100 100 26 15 20 30	250 100 160 250	
f_T	Transition Frequency	$I_C = 50\ mA$ $V_{CE} = 10\ V$	50			MHz
C_{CBO}	Collector-base Capacitance	$I_E = 0$ $V_{CB} = 10\ V$ $f = 1\ MHz$		12	25	pF
t_{on}	Turn-on Time	$I_C = 100\ mA$ $I_{B1} = 5\ mA$			250	ns
t_{off}	Turn-off Time	$I_C = 100\ mA$ $I_{B1} = I_{B2} = 5\ mA$			850	ns

* Pused : pulse duration = 300 μs , duty cycle = 1 %.

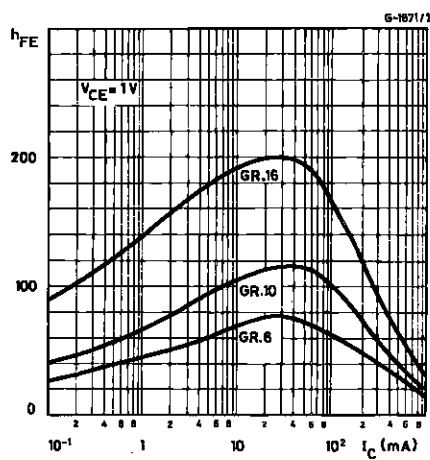
Collector-emitter Saturation Voltage.



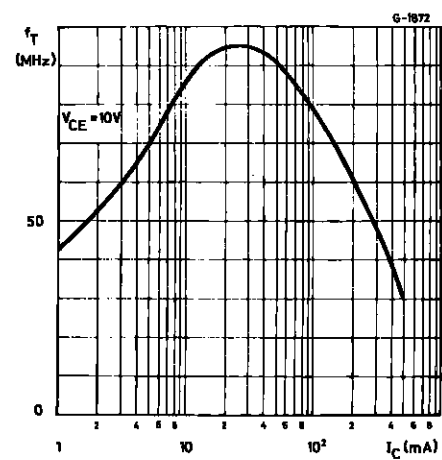
Base-emitter Voltage.



DC Current Gain.

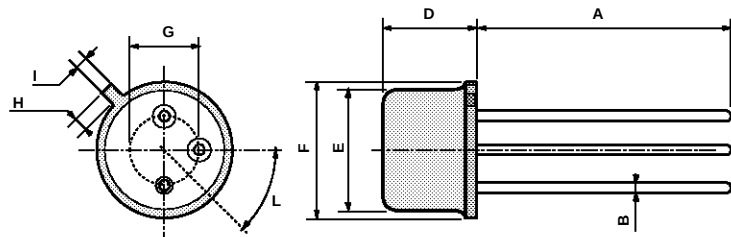


Transition Frequency.



TO39 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	12.7			0.500		
B			0.49			0.019
D			6.6			0.260
E			8.5			0.334
F			9.4			0.370
G	5.08			0.200		
H			1.2			0.047
I			0.9			0.035
L	45° (typ.)					



P008B

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